NSN 5962-01-176-5716

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View Online at https://aerobasegroup.com/nsn/5962-01-176-5716

Body Length: 1.290 inches **Body Width:** Between 0.500 inches and 0.610 inches **Body Height:** 0.210 inches **Maximum Power Dissipation Rating:** 1.0 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+125.0 degrees celsius **End Application:** Radar data transfer, subsystem an/gpn-2 (v) **Features Provided:** Hermetically sealed and burn in and ultraviolet erasable and monolithic and programmable **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** N-type metal oxide-semiconductor logic **Input Circuit Pattern:** 14 input **Case Outline Source And Designator:**

D-3 mil-m-38510

Current Rating Per Characteristic:

150.00 milliamperes supply

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

-0.3 volts power source and 6.0 volts power source

Time Rating Per Chacteristic:

250.00 nanoseconds propagation delay time, low to high level output and 250.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Prom

Test Data Document:

14933-80012 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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